

Evolution of structural and electrical properties of molecular layer deposited hafnicon films after thermal processing for applications in low-*k* etch stops

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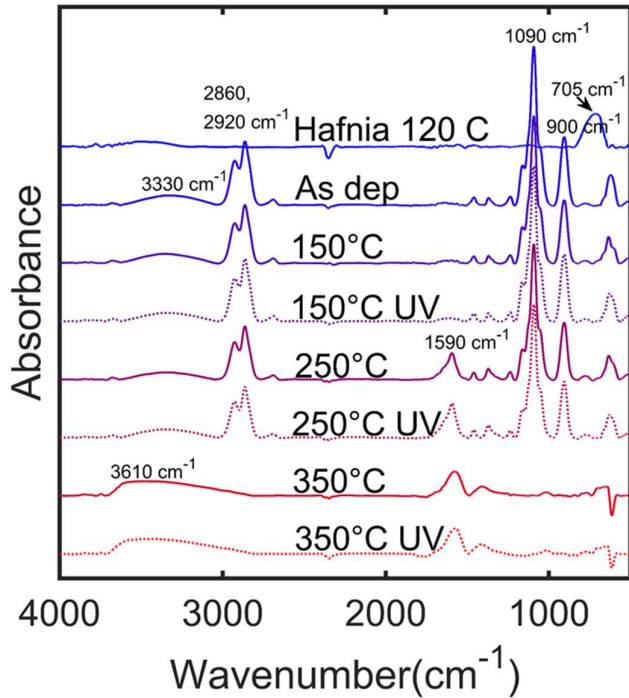


Figure 1: Ex-situ FTIR spectra of as-deposited and thermally processed hafnicon films compared to as-deposited hafnia film

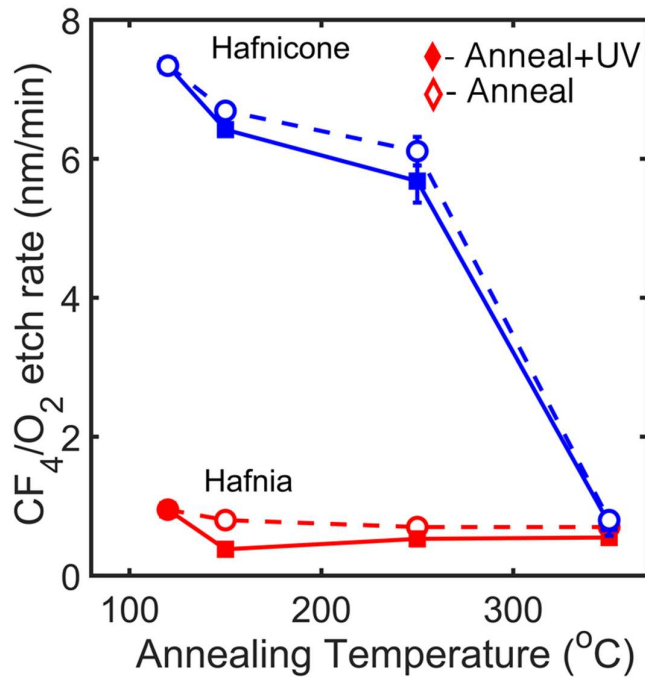


Figure 2: CF₄/O₂ plasma etch rate of as-deposited and thermally processed hafnicon films compared with hafnia

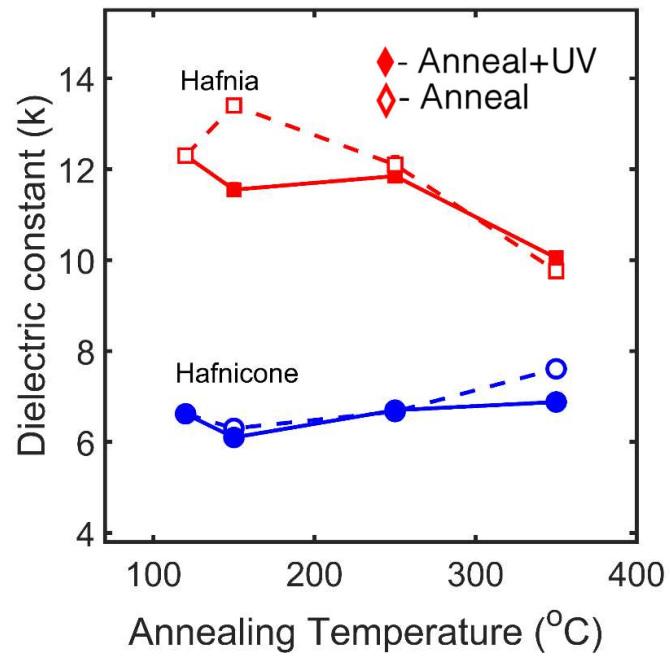


Figure 3: Dielectric constant vs annealing temperature of as-deposited and thermally processed hafnicon films compared to hafnia